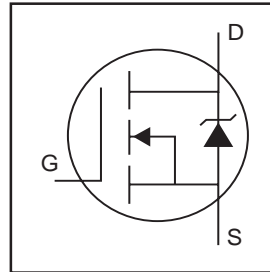


**Features**

- | Advanced Process Technology
- | Ultra Low On-Resistance
- | Dynamic dv/dt Rating
- | 175°C Operating Temperature
- | Fast Switching
- | Repetitive Avalanche Allowed up to Tjmax

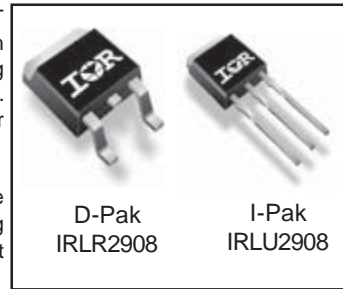


$V_{DSS} = 80V$
$R_{DS(on)} = 28m\Omega$
$I_D = 30A$

**Description**

Specifically designed for Automotive applications, this HEXFET® Power MOSFET utilizes the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of this HEXFET power MOSFET are a 175°C junction operating temperature, low RθJC, fast switching speed and improved repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in Automotive applications and a wide variety of other applications.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



**Absolute Maximum Ratings**

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Silicon Limited)	39	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (See Fig. 9)	28	
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$ (Package Limited)	30	
$I_{DM}$	Pulsed Drain Current ①	150	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	120	W
	Linear Derating Factor	0.77	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 16	V
$E_{AS}$	Single Pulse Avalanche Energy (Thermally Limited) ②	180	mJ
$E_{AS} (tested)$	Single Pulse Avalanche Energy Tested Value ⑦	250	
$I_{AR}$	Avalanche Current ①	See Fig.12a,12b,15,16	A
$E_{AR}$	Repetitive Avalanche Energy ⑥		mJ
dv/dt	Peak Diode Recovery dv/dt ③	2.3	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case )	

**Thermal Resistance**

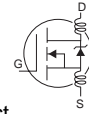
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.3	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ⑧	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

# IRLR2908/IRLU2908

International  
**IR** Rectifier

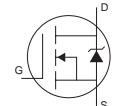
Static @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	80	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.085	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	22.5	28	mΩ	$V_{GS} = 10V, I_D = 23A$ ④
		—	25	30		$V_{GS} = 4.5V, I_D = 20A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	35	—	—	S	$V_{DS} = 25V, I_D = 23A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 80V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -16V$
$Q_g$	Total Gate Charge	—	22	33	nC	$I_D = 23A$
$Q_{gs}$	Gate-to-Source Charge	—	6.0	9.1		$V_{DS} = 64V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	11	17		$V_{GS} = 4.5V$
$t_{d(on)}$	Turn-On Delay Time	—	12	—		$V_{DD} = 40V$
$t_r$	Rise Time	—	95	—	ns	$I_D = 23A$
$t_{d(off)}$	Turn-Off Delay Time	—	36	—		$R_G = 8.3\Omega$
$t_f$	Fall Time	—	55	—		$V_{GS} = 4.5V$ ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	1890	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	260	—		$V_{DS} = 25V$
$C_{riss}$	Reverse Transfer Capacitance	—	35	—		$f = 1.0\text{MHz}$ , See Fig. 5
$C_{oss}$	Output Capacitance	—	1920	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	170	—		$V_{GS} = 0V, V_{DS} = 64V, f = 1.0\text{MHz}$
$C_{oss\ eff.}$	Effective Output Capacitance	—	310	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 64V$



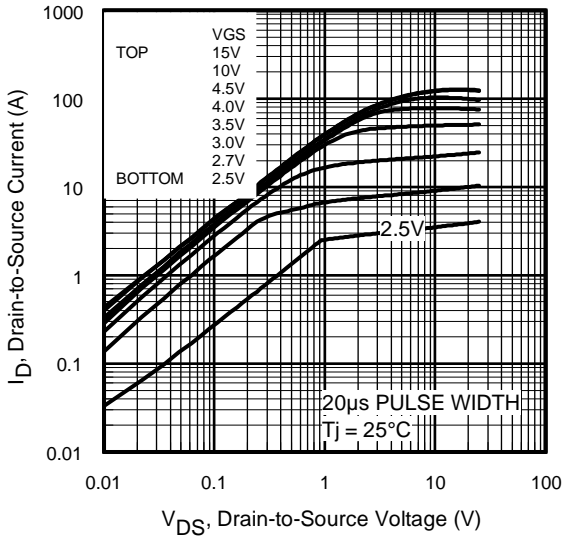
## Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	39	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	150		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 23A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	75	110	ns	$T_J = 25^\circ\text{C}, I_F = 23A, V_{DD} = 25V$
$Q_{rr}$	Reverse Recovery Charge	—	210	310	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S+L_D$ )				

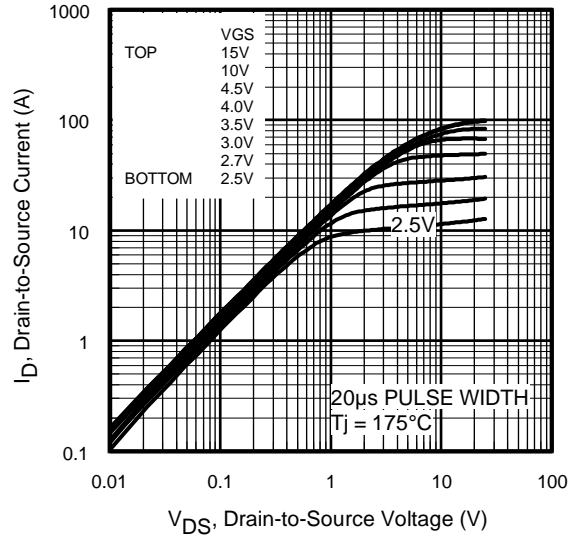


Notes ① through ⑧ are on page 11

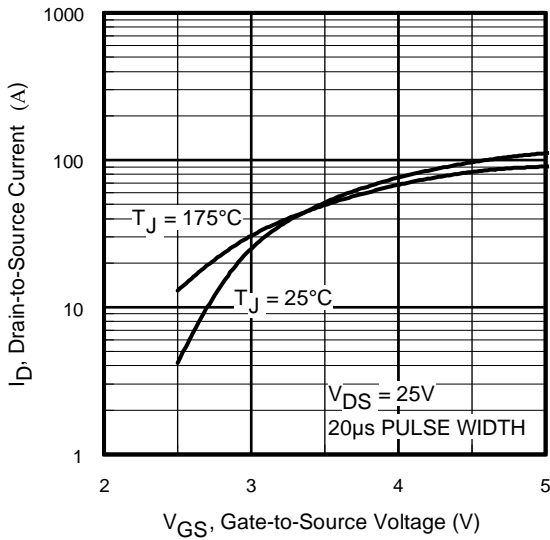
HEXFET® is a registered trademark of International Rectifier.



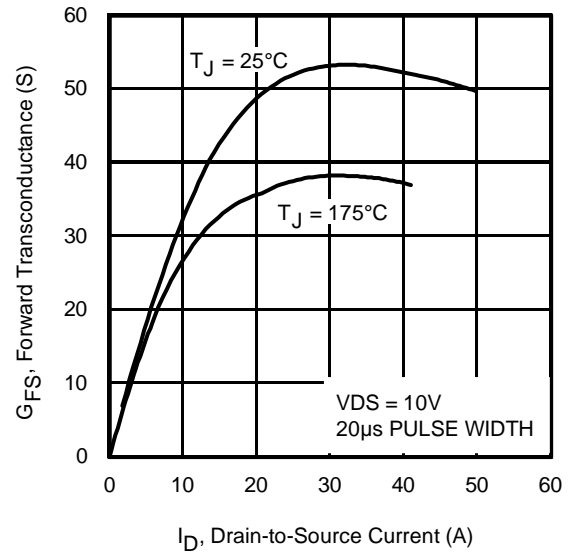
**Fig 1.** Typical Output Characteristics



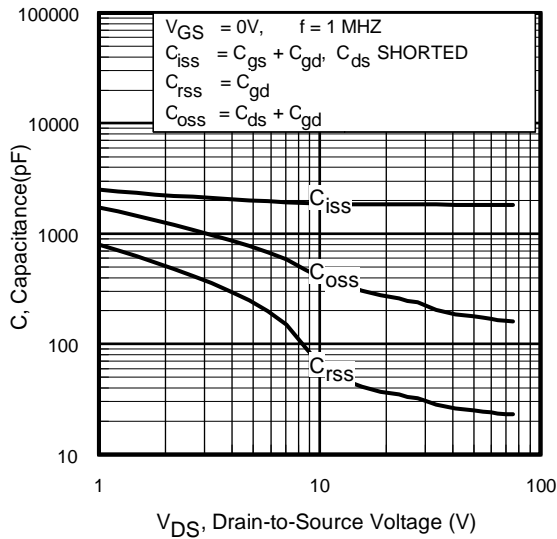
**Fig 2.** Typical Output Characteristics



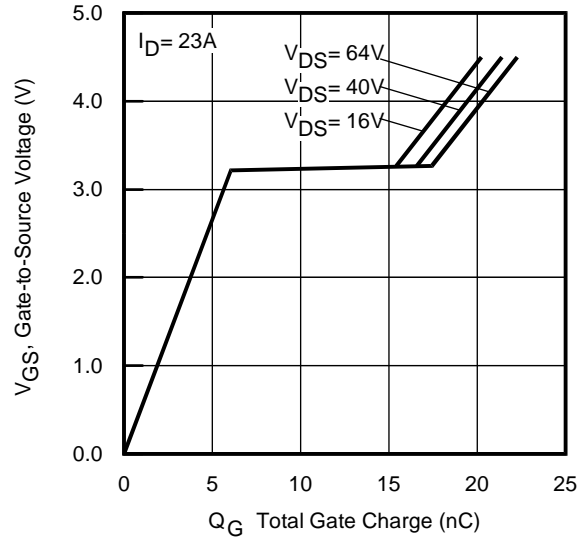
**Fig 3.** Typical Transfer Characteristics



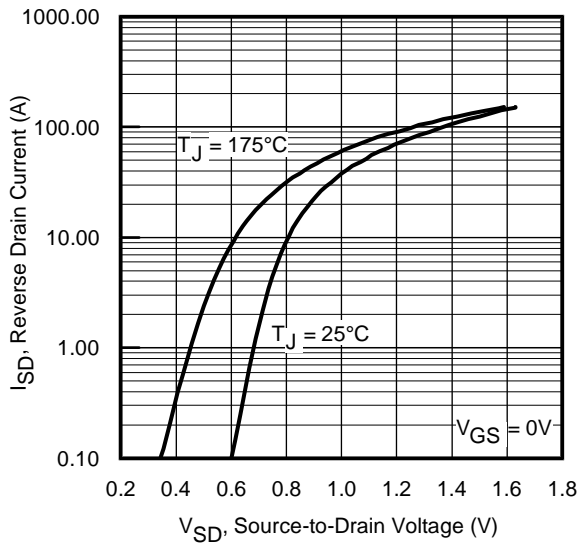
**Fig 4.** Typical Forward Transconductance vs. Drain Current



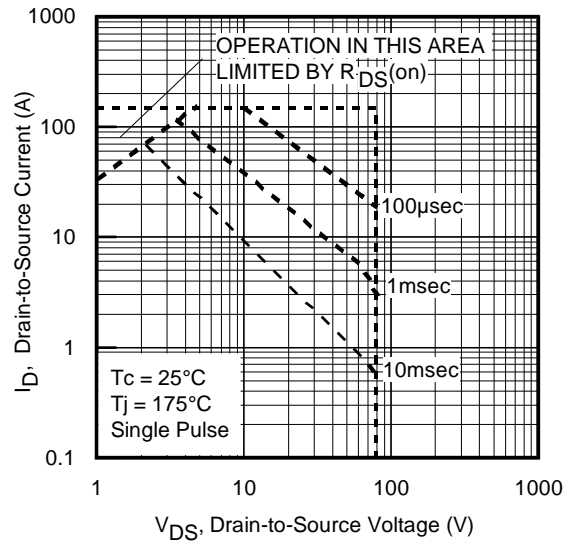
**Fig 5.** Typical Capacitance vs. Drain-to-Source Voltage



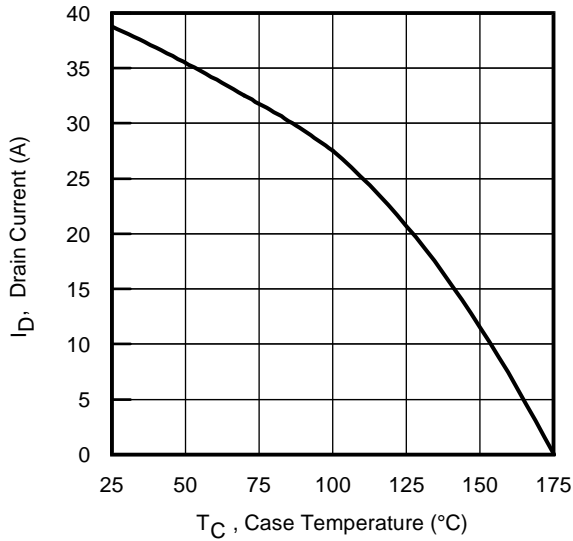
**Fig 6.** Typical Gate Charge vs. Gate-to-Source Voltage



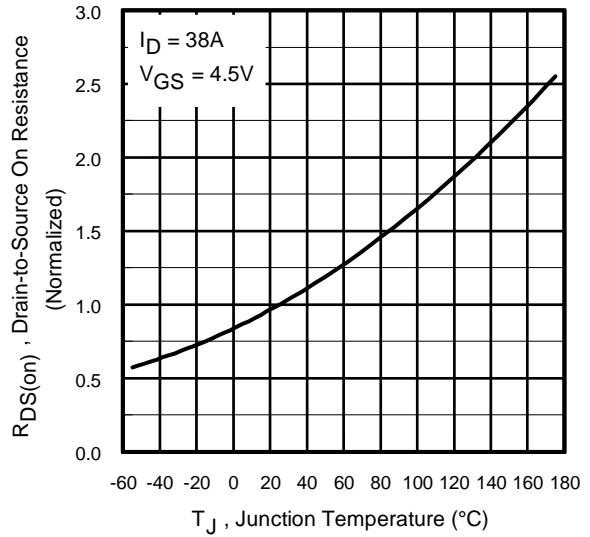
**Fig 7.** Typical Source-Drain Diode Forward Voltage



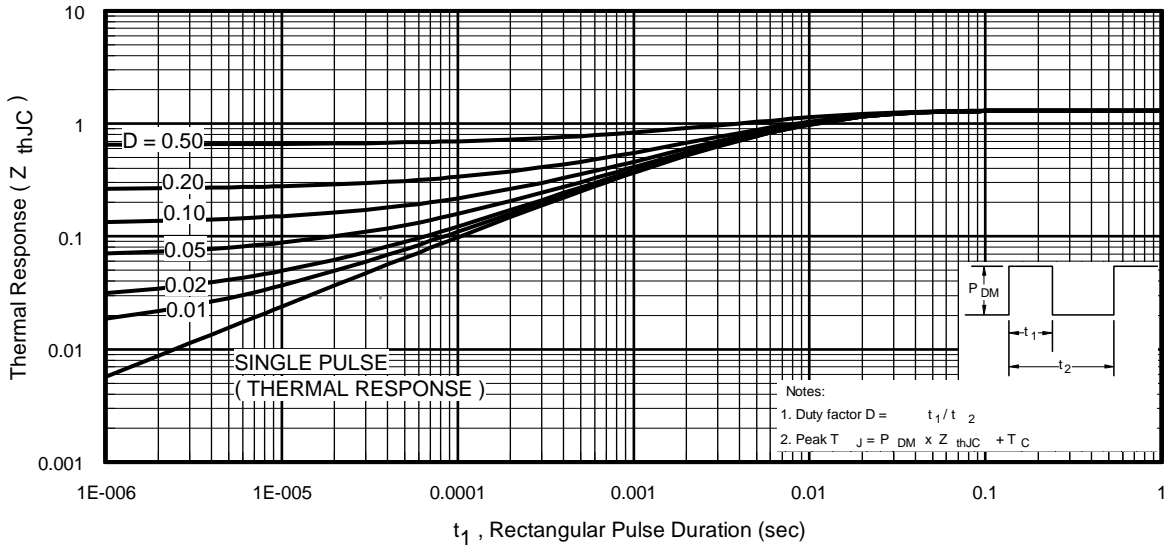
**Fig 8.** Maximum Safe Operating Area



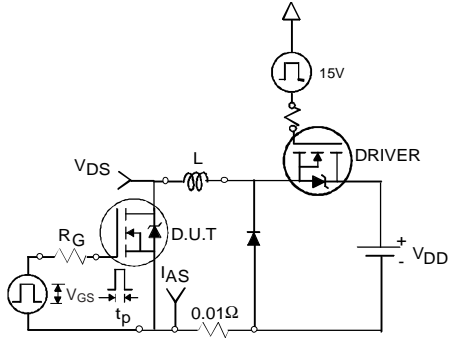
**Fig 9.** Maximum Drain Current vs. Case Temperature



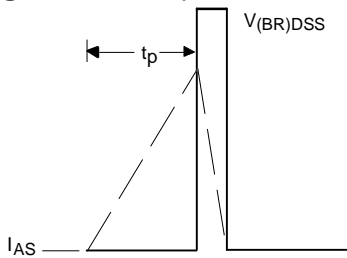
**Fig 10.** Normalized On-Resistance vs. Temperature



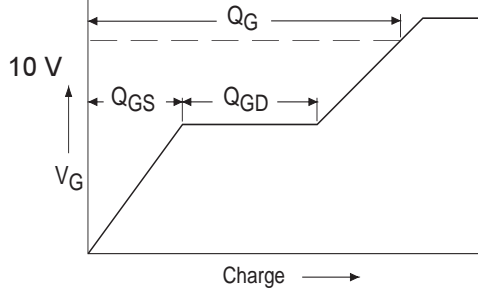
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



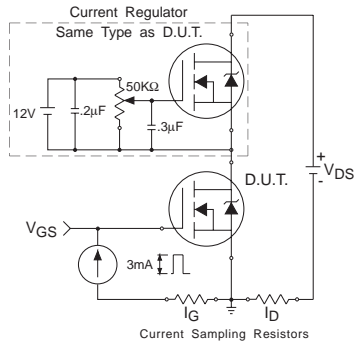
**Fig 12a.** Unclamped Inductive Test Circuit



**Fig 12b.** Unclamped Inductive Waveforms

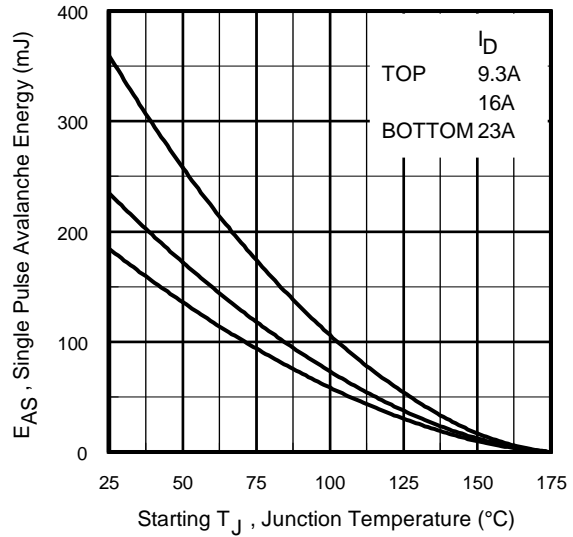


**Fig 13a.** Basic Gate Charge Waveform

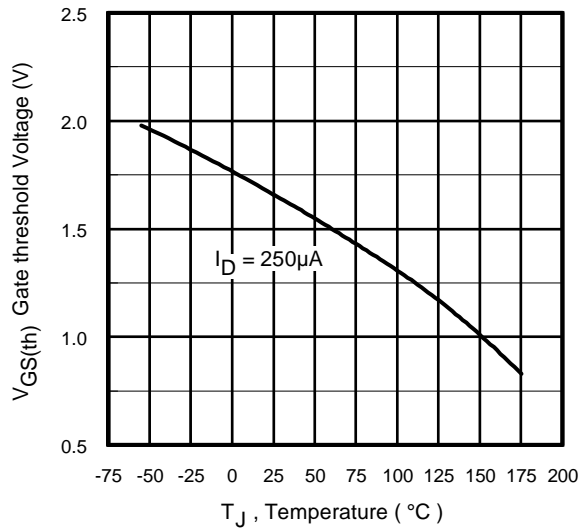


**Fig 13b.** Gate Charge Test Circuit

6



**Fig 12c.** Maximum Avalanche Energy vs. Drain Current



**Fig 14.** Threshold Voltage vs. Temperature

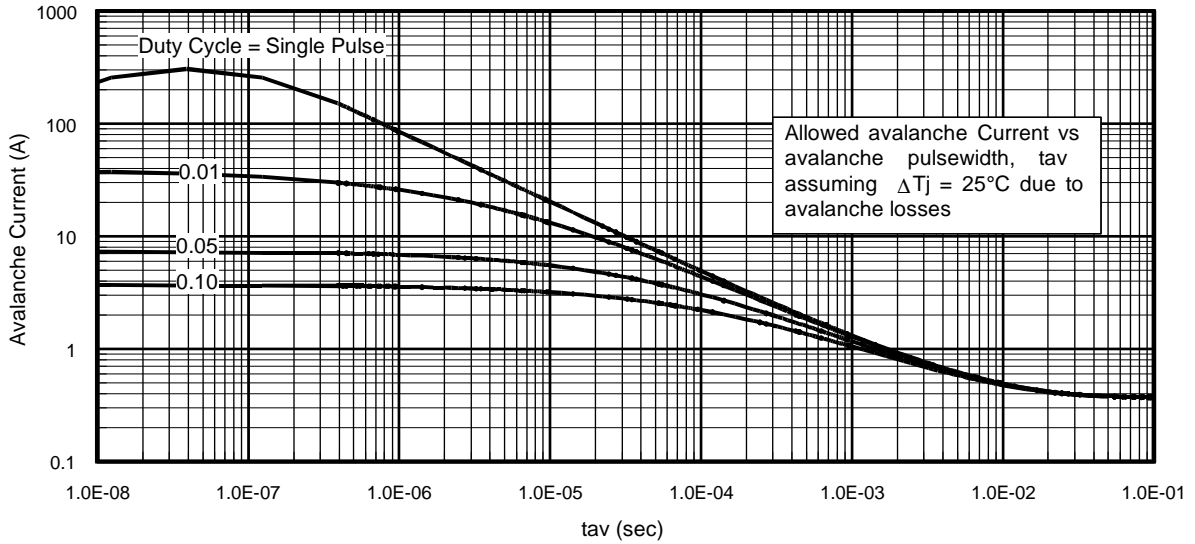


Fig 15. Typical Avalanche Current vs.Pulsewidth

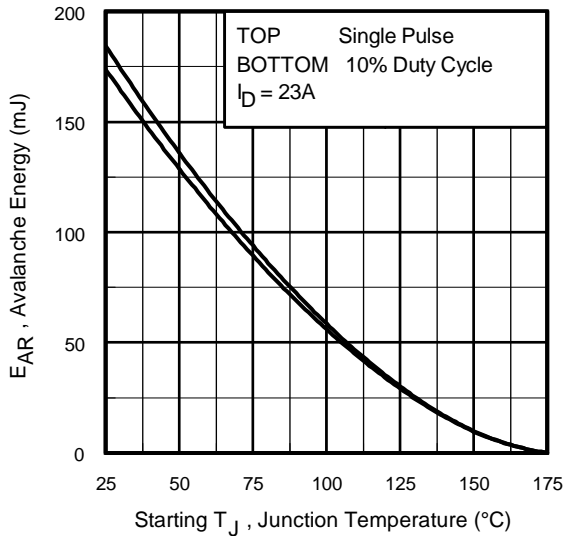


Fig 16. Maximum Avalanche Energy vs. Temperature

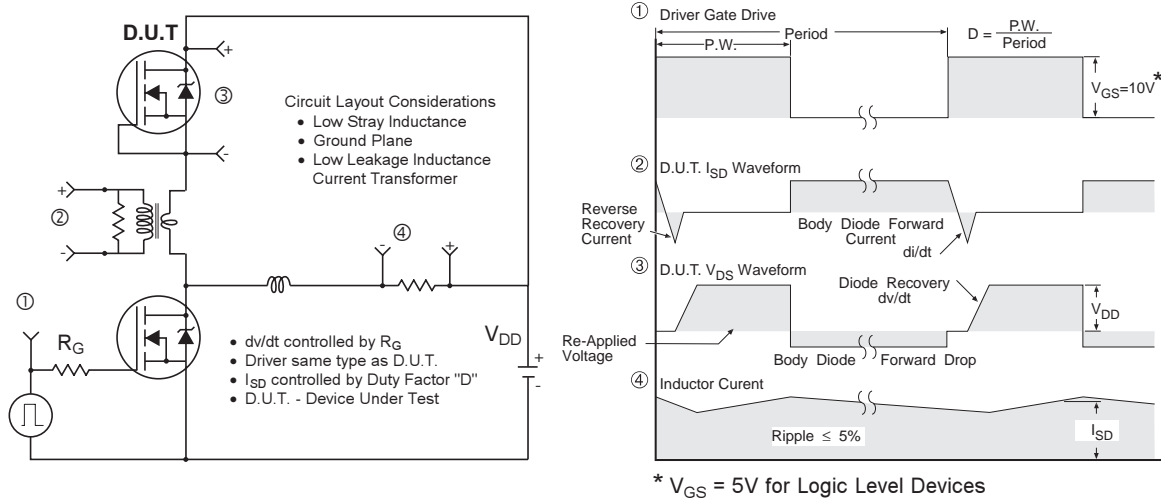
**Notes on Repetitive Avalanche Curves , Figures 15, 16:  
(For further info, see AN-1005 at www.irf.com)**

1. Avalanche failures assumption:  
Purely a thermal phenomenon and failure occurs at a temperature far in excess of  $T_{jmax}$ . This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as  $T_{jmax}$  is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4.  $P_{D(ave)}$  = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6.  $I_{av}$  = Allowable avalanche current.
7.  $\Delta T$  = Allowable rise in junction temperature, not to exceed  $T_{jmax}$  (assumed as 25°C in Figure 15, 16).  
 $t_{av}$  = Average time in avalanche.  
 $D$  = Duty cycle in avalanche =  $t_{av} \cdot f$   
 $Z_{thJC}(D, t_{av})$  = Transient thermal resistance, see figure 11)

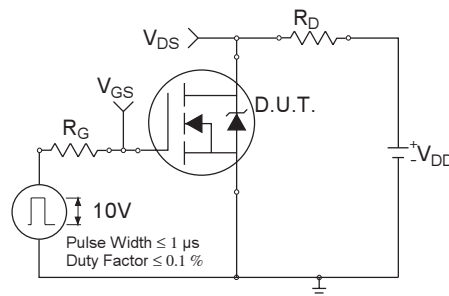
$$P_{D(ave)} = 1/2 ( 1.3 \cdot BV \cdot I_{av} ) = \Delta T / Z_{thJC}$$

$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$

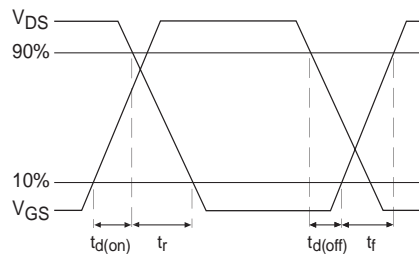
$$E_{AS(AR)} = P_{D(ave)} \cdot t_{av}$$



**Fig 17. Peak Diode Recovery  $dv/dt$  Test Circuit for N-Channel HEXFET® Power MOSFETs**



**Fig 18a. Switching Time Test Circuit**

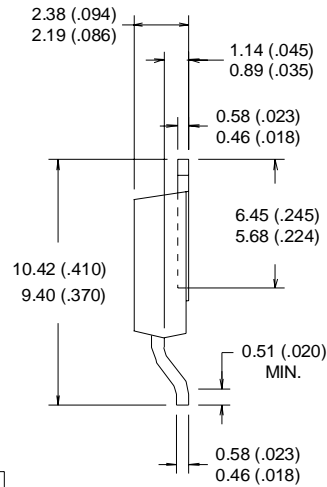
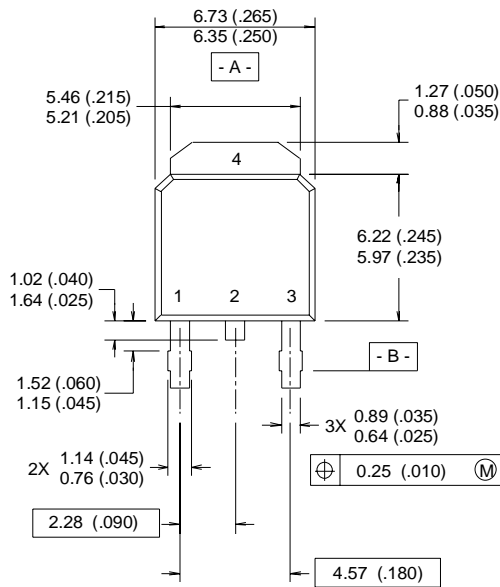


**Fig 18b. Switching Time Waveforms**



## TO-252AA (D-Pak) Package Outline

Dimensions are shown in millimeters (inches)



### LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE
- 4 - DRAIN

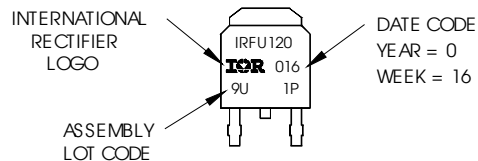
### NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH.
- 3 CONFORMS TO JEDEC OUTLINE TO-252AA.
- 4 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP, SOLDER DIP MAX. +0.16 (.006).

## TO-252AA (D-Pak) Part Marking Information

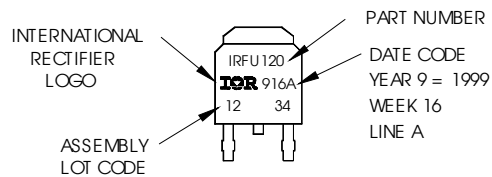
Notes: This part marking information applies to devices produced before 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 9U1P



Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"

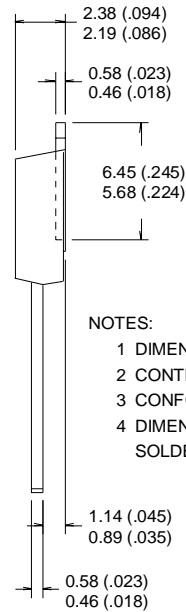
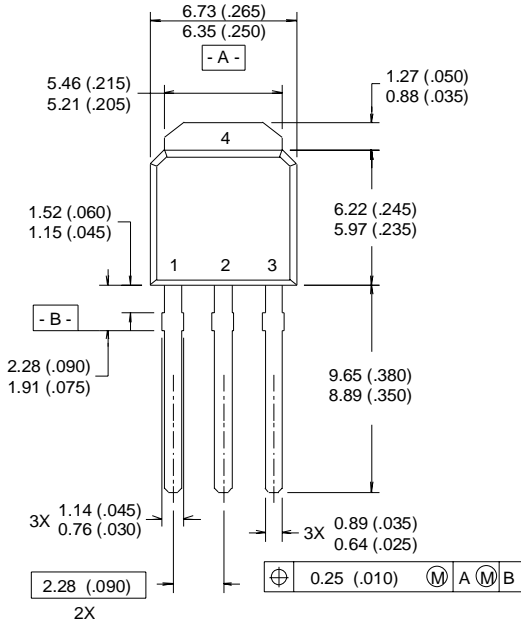


# IRLR2908/IRLU2908



## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



### LEAD ASSIGNMENTS

- 1 - GATE
- 2 - DRAIN
- 3 - SOURCE
- 4 - DRAIN

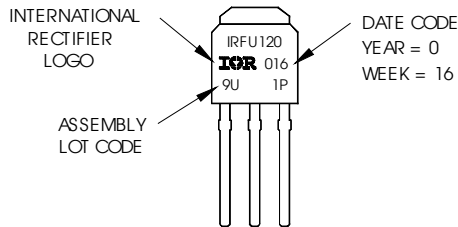
### NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH.
- 3 CONFORMS TO JEDEC OUTLINE TO-252AA.
- 4 DIMENSIONS SHOWN ARE BEFORE SOLDER DIP, SOLDER DIP MAX. +0.16 (.006).

## I-Pak (TO-251AA) Part Marking Information

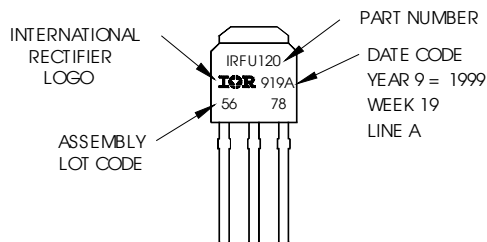
Notes: This part marking information applies to devices produced before 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 9U1P



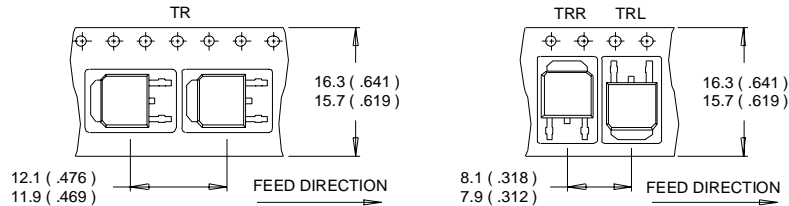
Notes: This part marking information applies to devices produced after 02/26/2001

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 5678  
ASSEMBLED ON WW 19, 1999  
IN THE ASSEMBLY LINE "A"

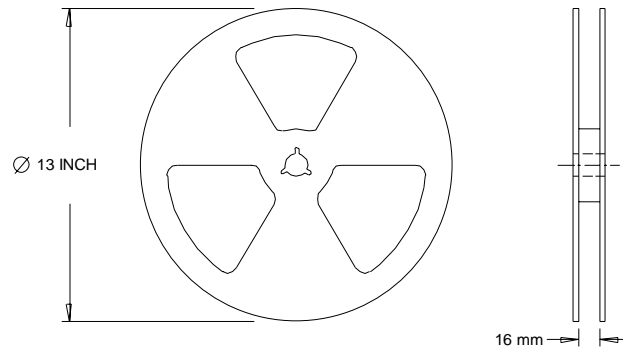


## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② Limited by  $T_{Jmax}$ , starting  $T_J = 25^\circ C$ ,  $L = 0.71mH$ ,  $R_G = 25\Omega$ ,  $I_{AS} = 23A$ ,  $V_{GS} = 10V$ . Part not recommended for use above this value.
- ③  $I_{SD} \leq 23A$ ,  $di/dt \leq 400A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  $T_J \leq 175^\circ C$ .
- ④ Pulse width  $\leq 1.0ms$ ; duty cycle  $\leq 2\%$ .
- ⑤  $C_{oss}$  eff. is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .
- ⑥ Limited by  $T_{Jmax}$ , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
- ⑦ This value determined from sample failure population. 100% tested to this value in production.
- ⑧ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Automotive [Q101] market.  
 Qualification Standards can be found on IR's Web site.